

isc Silicon NPN Darlington Power Transistor

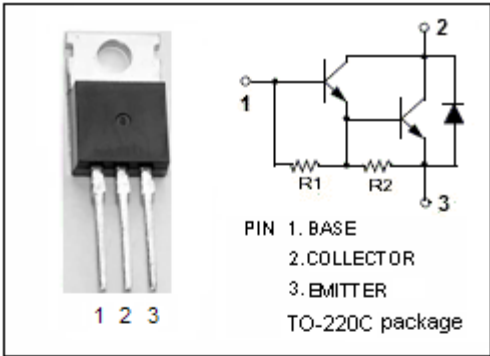
2SD833

DESCRIPTION

- High DC Current Gain-
: $h_{FE}=4000(\text{Min}) @ I_C=3A$
- Low Collector Saturation Voltage-
: $V_{CE(sat)}=1.5V(\text{Max.}) @ I_C=3A$

APPLICATIONS

- Audio power amplifiers
- Relay& solenoid drivers
- Motor controls
- General purpose power amplifiers

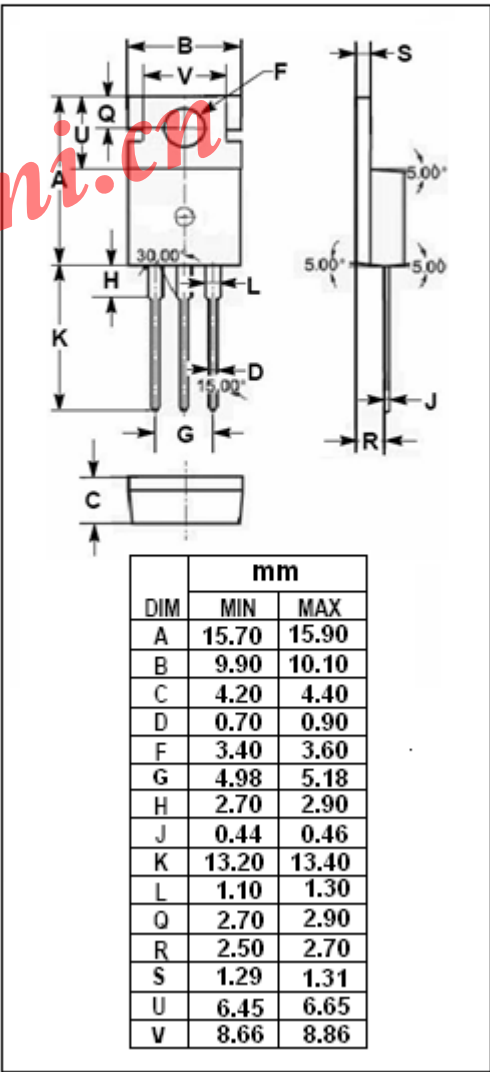


ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
$V_{CEO(SUS)}$	Collector-Emitter Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	7	A
I_B	Base Current-Continuous	0.2	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	40	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	3.0	$^{\circ}C/W$



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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=0.1\text{A}; I_B=0$	50			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=0.1\text{mA}; I_B=0$	60			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=0.1\text{mA}; I_E=0$	60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=3\text{mA}; I_C=0$	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=6\text{mA}$			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=6\text{mA}$			2.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=60\text{V}; I_E=0$			0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			3.0	mA
h_{FE}	DC Current Gain	$I_C=3\text{A}; V_{CE}=3\text{V}$	4000			